## UP04111G

#### Silicon PNP epitaxial planar type

#### For switching/digital circuits

#### Features

- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

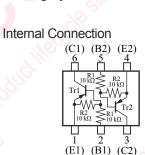
• UNR2111 × 2

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V
Collector current	I <sub>C</sub>	-100	mA
Total power dissipation	P <sub>T</sub>	125	mW
Junction temperature	Tj	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

# Package Code SSMini6-F2 Pin Name

- 1: Emitter (Tr1)4: Emitter (Tr2)2: Base (Tr1)5: Base (Tr2)3: Collector (Tr2)6: Collector (Tr1)
- Marking Symbol: 9U



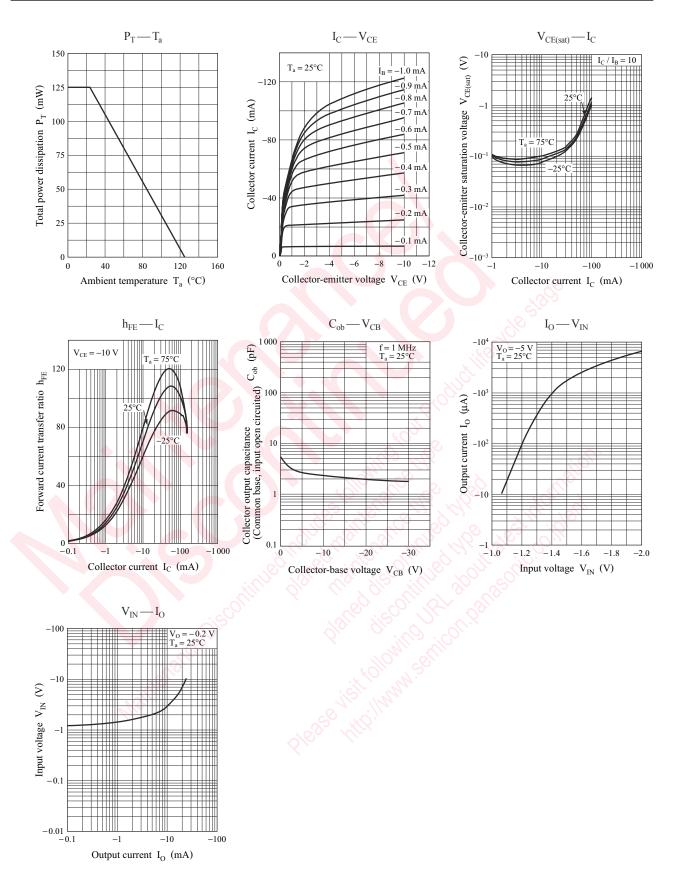
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	<ul> <li>Min</li> </ul>	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \mu {\rm A}, I_{\rm E} = 0$	-50	5	Ĉ,	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2  {\rm mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{\rm CB} = -50$ V, $I_{\rm E} = 0$	Ser as	2	- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{\rm CE} = -50 \text{ V}, I_{\rm B} = 0$	Shio.		- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{\rm EB} = -6 \text{ V}, I_{\rm C} = 0$	,X		- 0.5	mA
Forward current transfer ratio	$\mathbf{h}_{\mathrm{FE}}$	$V_{\rm CE} = -10$ V, $I_{\rm C} = -5$ mA	35			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			-0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -0.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -2.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R <sub>1</sub>	0/6,02 him	-30%	10	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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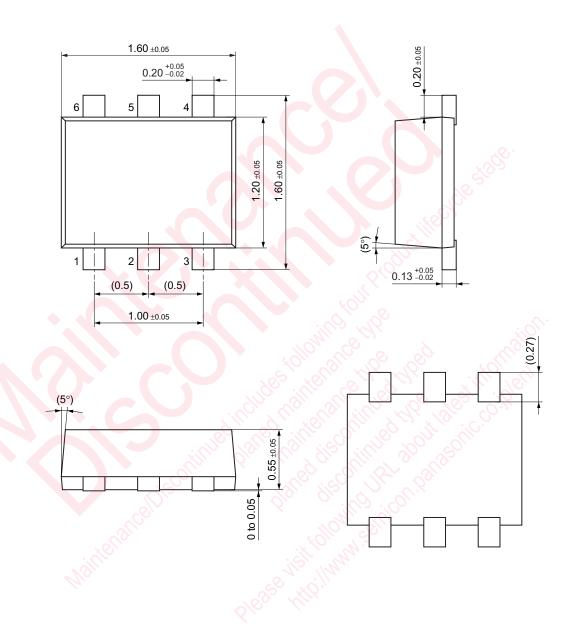
### **Panasonic**



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## SSMini6-F2

Unit: mm



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